

2N6426*, 2N6427

Preferred Device

Darlington Transistors

NPN Silicon

Features

- Pb-Free Packages are Available**
- Device Marking: Device Type, e.g., 2N6426, Date Code



ON Semiconductor®

<http://onsemi.com>

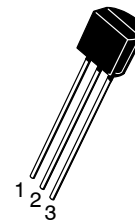
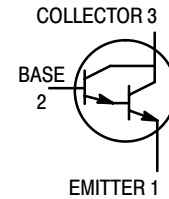
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	40	Vdc
Collector – Base Voltage	V_{CBO}	40	Vdc
Emitter – Base Voltage	V_{EBO}	12	Vdc
Collector Current – Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

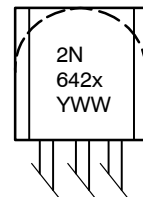
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$



TO-92
CASE 29
STYLE 1

MARKING DIAGRAM



642x Specific Device Code
Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 120 of this data sheet.

*Preferred devices are recommended choices for future use and best overall value.

**For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

2N6426*, 2N6427

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage, (Note 2) (I _C = 10 mA _{dc} , V _{BE} = 0)	V _{(BR)CEO}	40	–	–	V _{dc}
Collector–Base Breakdown Voltage (I _C = 100 μA _{dc} , I _E = 0)	V _{(BR)CBO}	40	–	–	V _{dc}
Emitter–Base Breakdown Voltage (I _E = 10 μA _{dc} , I _C = 0)	V _{(BR)EBO}	12	–	–	V _{dc}
Collector Cutoff Current (V _{CE} = 25 V _{dc} , I _B = 0)	I _{CES}	–	–	1.0	μA _{dc}
Collector Cutoff Current (V _{CB} = 30 V _{dc} , I _E = 0)	I _{CBO}	–	–	50	nA _{dc}
Emitter Cutoff Current (V _{EB} = 10 V _{dc} , I _C = 0)	I _{EBO}	–	–	50	nA _{dc}
ON CHARACTERISTICS					
DC Current Gain, (Note 2) (I _C = 10 mA _{dc} , V _{CE} = 5.0 V _{dc})	h _{FE}	20,000 10,000	– –	200,000 100,000	–
(I _C = 100 mA _{dc} , V _{CE} = 5.0 V _{dc})		30,000 20,000	– –	300,000 200,000	
(I _C = 500 mA _{dc} , V _{CE} = 5.0 V _{dc})		20,000 14,000	– –	200,000 140,000	
Collector–Emitter Saturation Voltage (I _C = 50 mA _{dc} , I _B = 0.5 mA _{dc}) (I _C = 500 mA _{dc} , I _B = 0.5 mA _{dc})	V _{CE(sat)}	– –	0.71 0.9	1.2 1.5	V _{dc}
Base–Emitter Saturation Voltage (I _C = 500 mA _{dc} , I _B = 0.5 mA _{dc})	V _{BE(sat)}	–	1.52	2.0	V _{dc}
Base–Emitter On Voltage (I _C = 50 mA _{dc} , V _{CE} = 5.0 V _{dc})	V _{BE(on)}	–	1.24	1.75	V _{dc}
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance (V _{CB} = 10 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{obo}	–	5.4	7.0	pF
Input Capacitance (V _{EB} = 1.0 V _{dc} , I _C = 0, f = 1.0 MHz)	C _{ibo}	–	10	15	pF
Input Impedance (I _C = 10 mA _{dc} , V _{CE} = 5.0 V _{dc} , f = 1.0 kHz)	h _{ie}	100 50	– –	2000 1000	kΩ
Small–Signal Current Gain (I _C = 10 mA _{dc} , V _{CE} = 5.0 V _{dc} , f = 1.0 kHz)	h _{fe}	20,000 10,000	– –	– –	–
Current–Gain – High Frequency (I _C = 10 mA _{dc} , V _{CE} = 5.0 V _{dc} , f = 100 MHz)	h _{fe}	1.5 1.3	2.4 2.4	– –	–
Output Admittance (I _C = 10 mA _{dc} , V _{CE} = 5.0 V _{dc} , f = 1.0 kHz)	h _{oe}	–	–	1000	μmhos
Noise Figure (I _C = 1.0 mA _{dc} , V _{CE} = 5.0 V _{dc} , R _S = 100 kΩ, f = 1.0 kHz)	NF	–	3.0	10	dB

2. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.

2N6426*, 2N6427

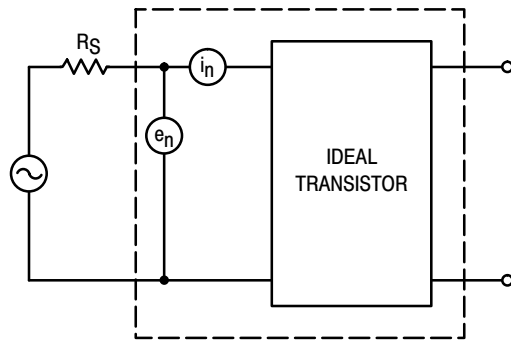


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

($V_{CE} = 5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

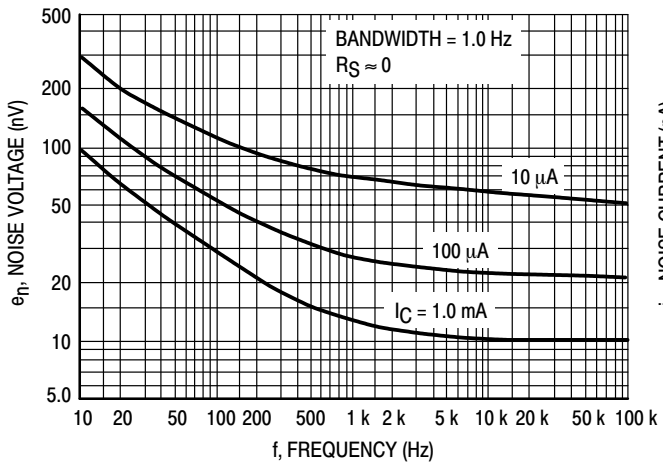


Figure 2. Noise Voltage

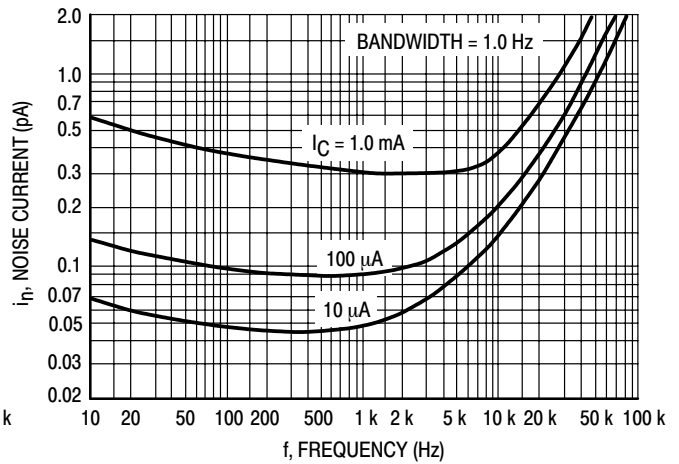


Figure 3. Noise Current

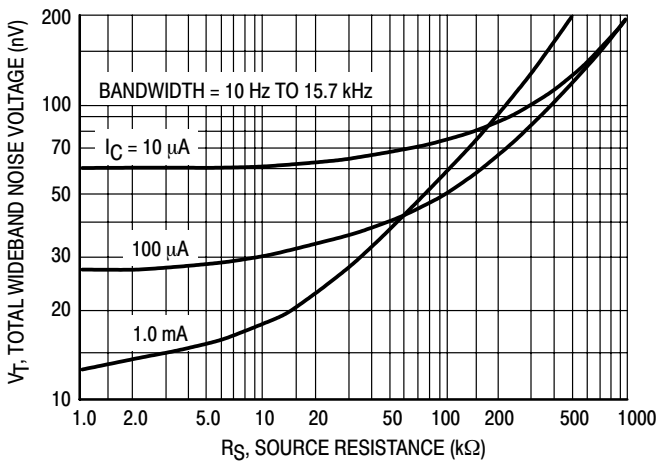


Figure 4. Total Wideband Noise Voltage

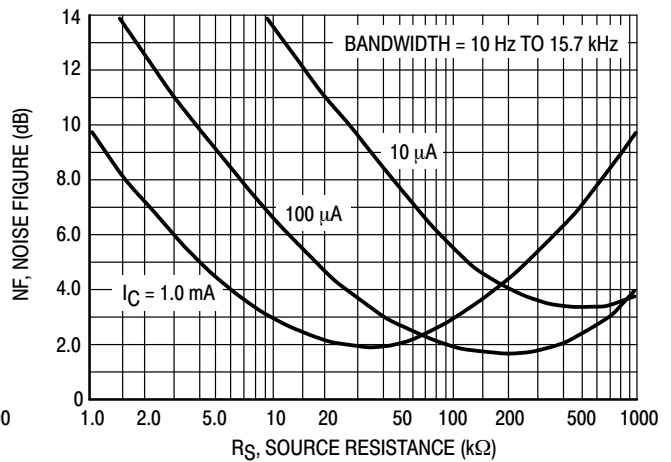


Figure 5. Wideband Noise Figure

SMALL-SIGNAL CHARACTERISTICS

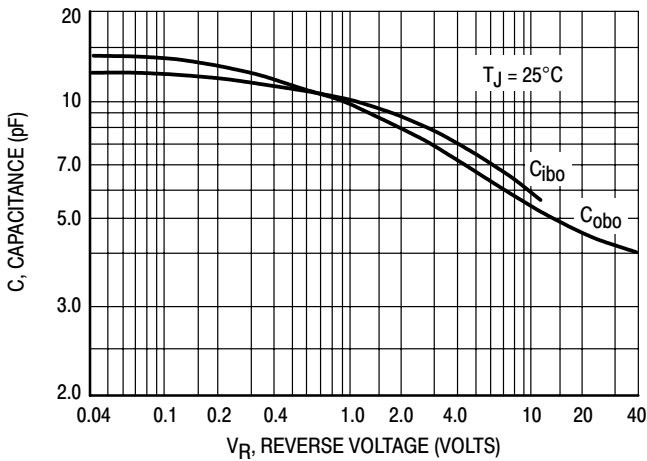


Figure 6. Capacitance

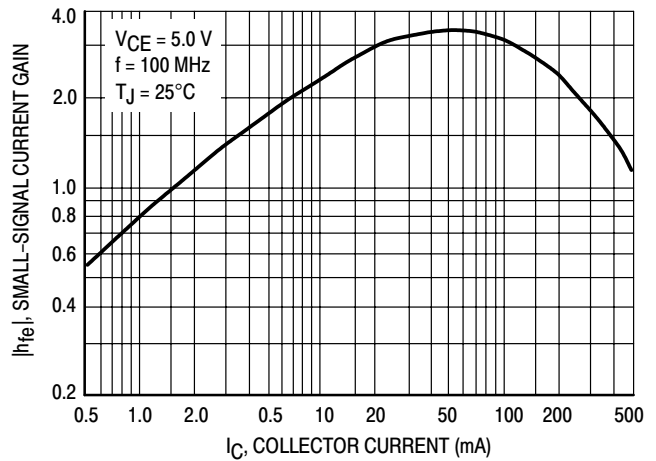


Figure 7. High Frequency Current Gain

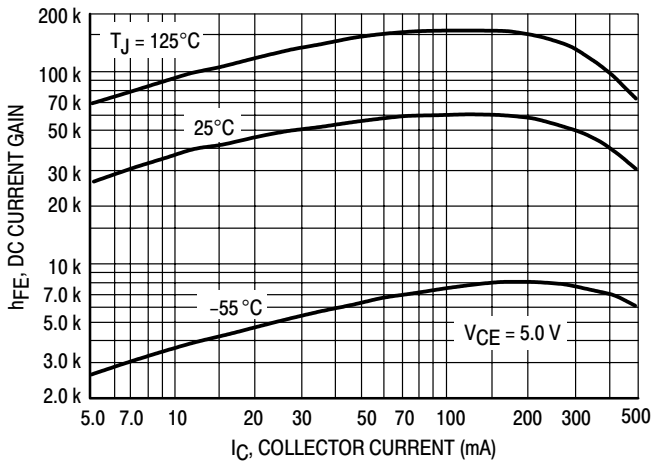


Figure 8. DC Current Gain

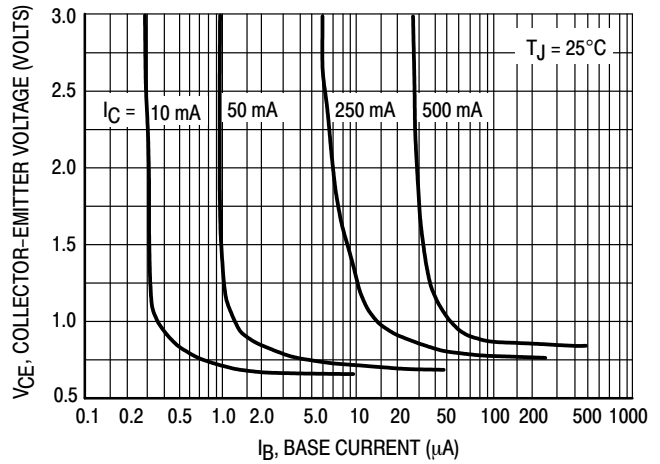


Figure 9. Collector Saturation Region

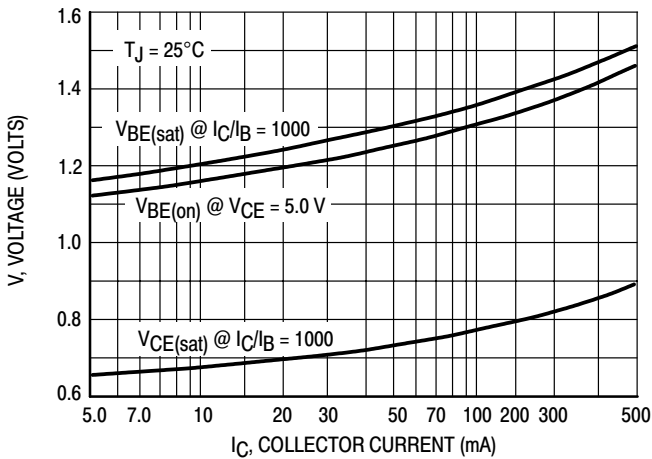


Figure 10. "On" Voltages

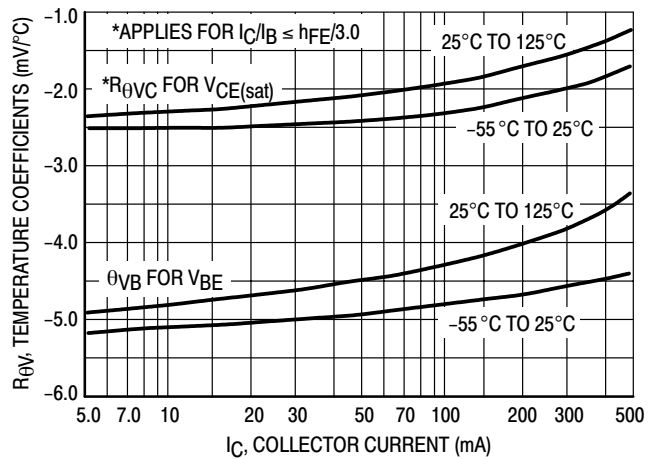


Figure 11. Temperature Coefficients

2N6426*, 2N6427

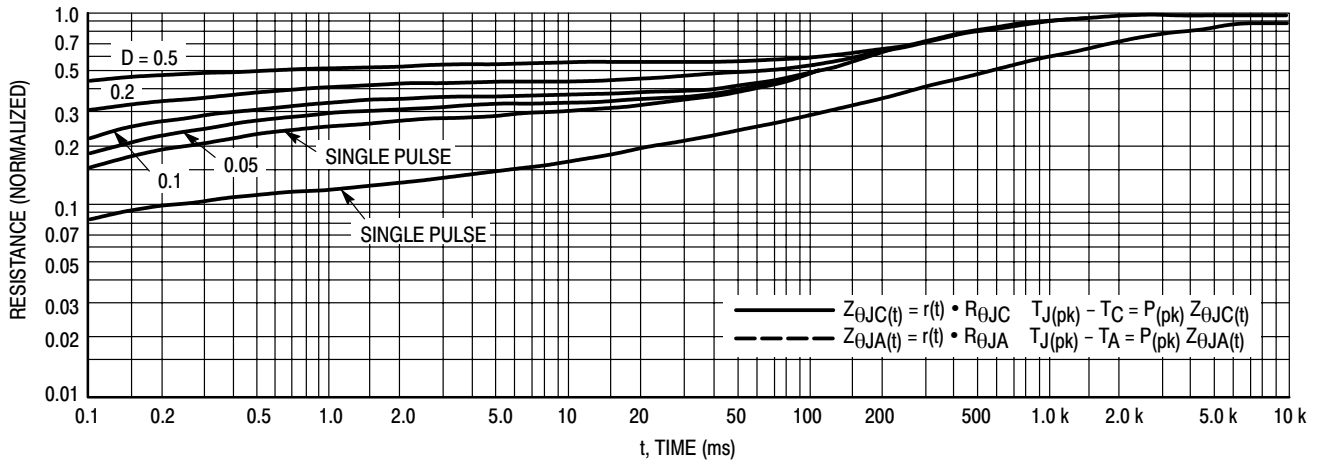


Figure 12. Thermal Response

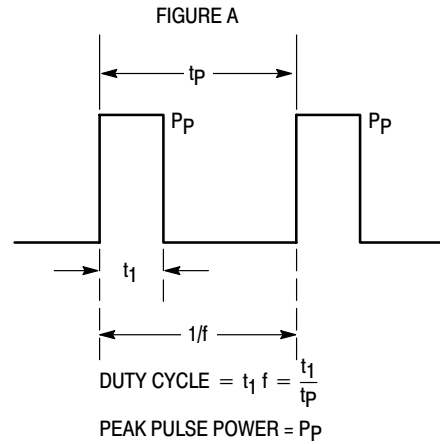
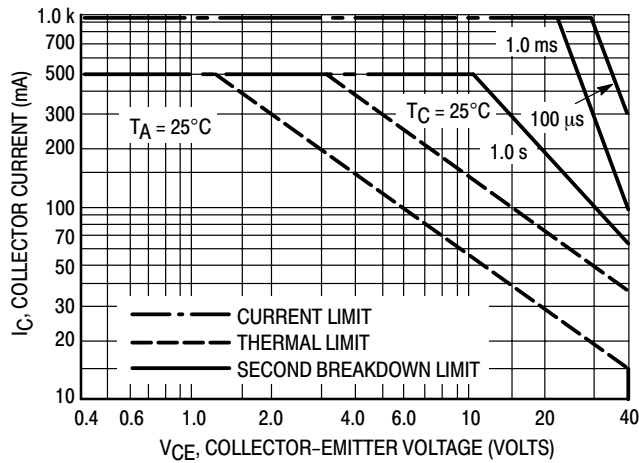


Figure 13. Active Region Safe Operating Area Design Note: Use of Transient Thermal Resistance Data

ORDERING INFORMATION

Device	Package	Shipping†
2N6426	TO-92	5,000 Units / Box
2N6426G	TO-92 (Pb-Free)	5,000 Units / Box
2N6426RLRA	TO-92	2,000 / Tape & Reel
2N6427	TO-92	5,000 Units / Box
2N6427RLRA	TO-92	2,000 / Tape & Reel
2N6427RLRAG	TO-92 (Pb-Free)	2,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.